

## RB521S-40 SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

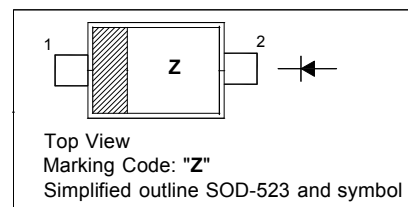
for rectifying small power applications

### Features

- Ultra small mold type
- Low forward voltage
- High reliability

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



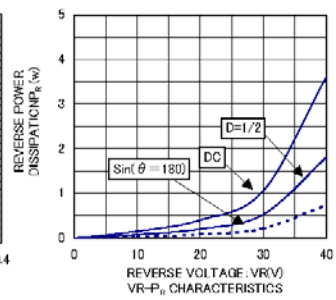
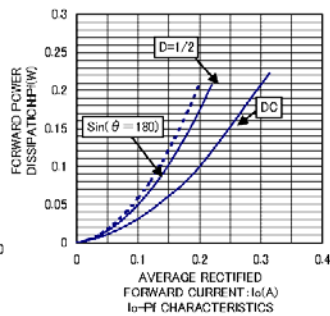
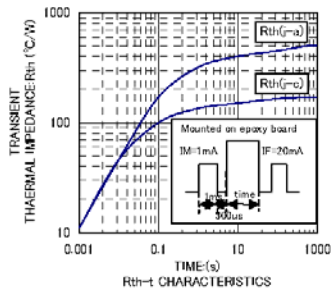
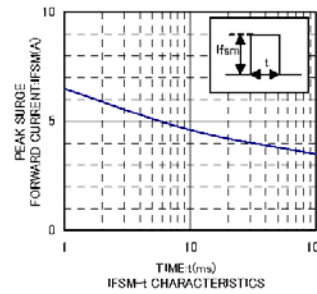
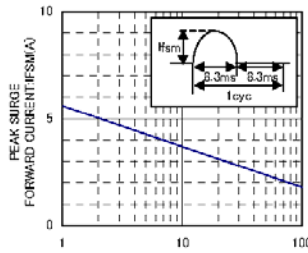
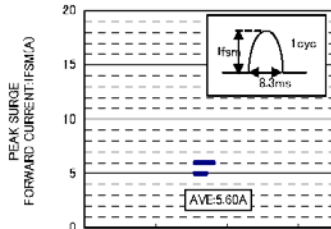
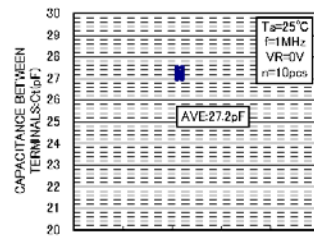
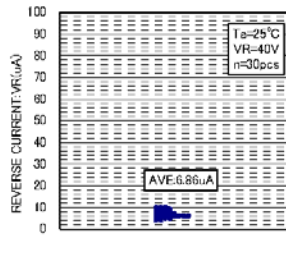
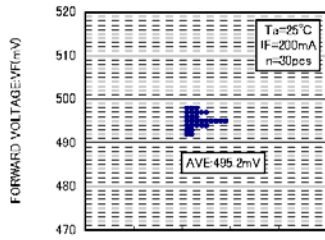
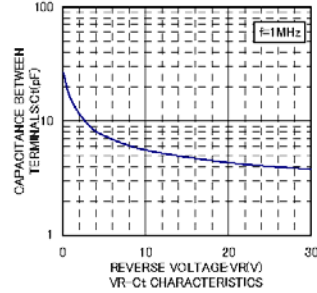
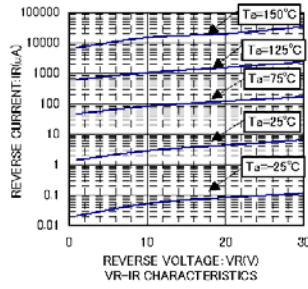
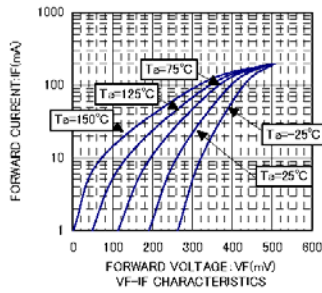
### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RM}$	45	V
Reverse Voltage	$V_R$	40	V
Mean Rectifying Current	$I_O$	200	mA
Peak Forward Surge Current (60Hz for Cyc.)	$I_{FSM}$	1	A
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$ at $I_F = 100\text{ mA}$ at $I_F = 200\text{ mA}$	$V_F$	0.16 0.31 0.41	0.3 0.45 0.54	V
Reverse Current at $V_R = 10\text{ V}$ at $V_R = 40\text{ V}$	$I_R$	- -	20 90	$\mu\text{A}$

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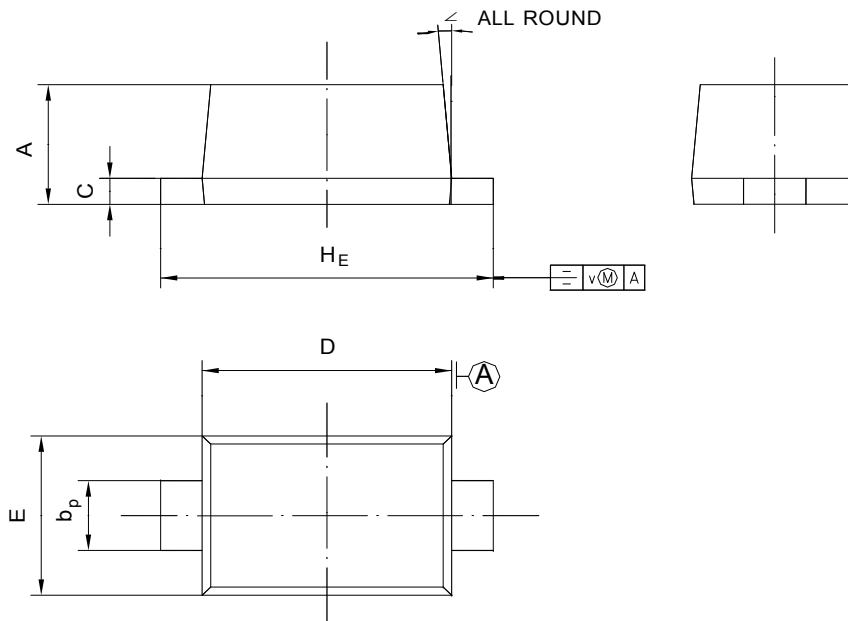


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## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



UNIT	A	b <sub>p</sub>	C	D	E	H <sub>E</sub>	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°